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		OTHER PRIOR ART NON PATENT LITERATURE DOCUMENTS			
Examiner Cite No.1					
S.J.L.	L	International Work Shop 157nm Lithography MIT-LL, Boston, MA, May 5, 1999			
	м	Kunz et al. "Outlook for 157 nm Resist Design," J. Vac. Sci. Technol. B 17(6), Nov/Dec 1999, pp. 3267-3272			
	N	Chiba et al., "157 nm Resist Materials: A Progress Report," J. Photopolymer Science and Technology, Vol. 13, No. 4 (2000) pp 657-664			
	.0	Schmaljohann et al., "Fundamental Studies of Fluoropolymer Photoresists for 157 nm Lithography," <i>J. of Photopolymer Science Technology</i> , Vol., 13, No. 3 (2000) pp 451-458			
	Р	Brunsvold et al., "Evaluation of a Deep UV Bilayer Resist for Sub-Half Micron Lithography," SPIE Vol. 1925 (1993), pp. 377-387			
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	U	Boardman et al., "Chemical Aspects of Silicon-Containing Bilayer Resists" SPIE Vol. 3678 (1999) pp. 562-572			
	V	Kim et al., "Chemically amplified resist based on the methacrylate polymer with 2-trimethylsilyl-2-propyl ester protecting group" SPIE Vol. 3678 (1999) pp 420-428			

Examiner Signature	Sã.	A. Lee	Date Considered	9-25-03	

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